

0.8 A 400 V high immunity sensitive SCR thyristor in TO-92

## Features

- On-state rms current,  $I_{T(RMS)}$  0.8 A
- 125 °C max.  $T_j$
- Low 0.2 mA gate current
- Repetitive peak off-state voltage,  $V_{DRM}/V_{RRM}$  400 V
- ECOPACK2 compliant

## Applications

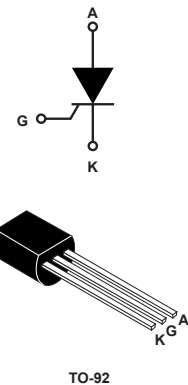
- Gate driver for large Thyristors
- Overvoltage crowbar protection
- Ground fault circuit interrupters
- Arc fault circuit interrupter
- Standby mode power supplies
- Residual current detector

## Description

Thanks to highly sensitive triggering levels, the 0.8 A P0102DA SCR thyristor is suitable for all applications where available gate current is limited.

This device offers a high blocking voltage of 400 V, ideal for applications like interrupters circuits.

The P0102DA is available in through-hole TO-92 package.



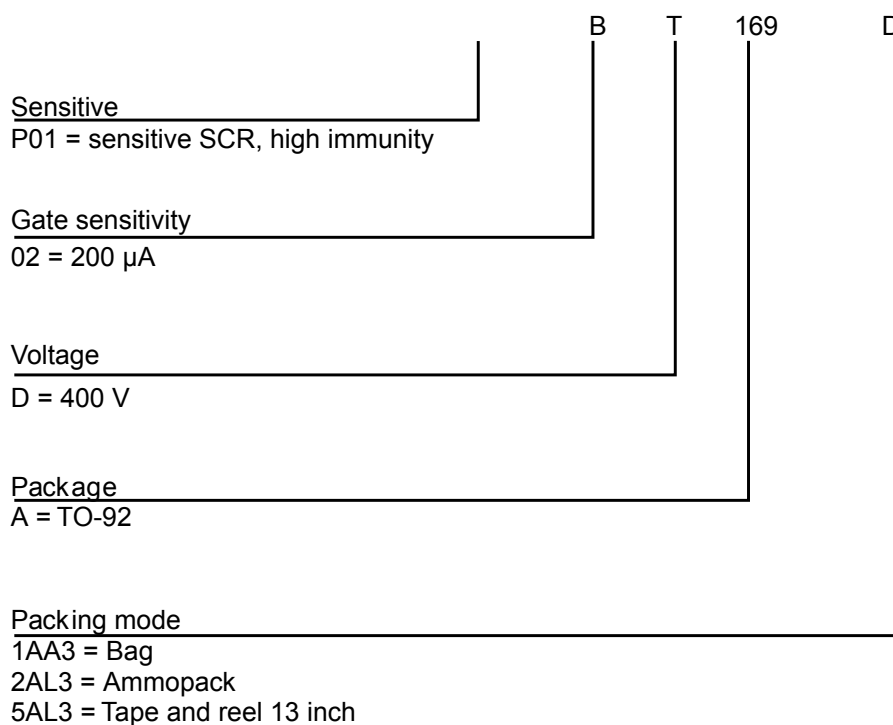
Product status link

[P0102DA](#)

Product summary

$I_{T(RMS)}$	0.8 A
$V_{DRM}/V_{RRM}$	400 V
$I_{GT}$	0.2 mA
$T_{jmax.}$	125 °C

Figure 1. Ordering information scheme



## 1 Characteristics

**Table 1. Absolute maximum ratings (limiting values)**

Symbol	Parameters	Value	Unit		
$I_{T(RMS)}$	On-state RMS current (180° conduction angle)	$T_L = 55\text{ °C}$	0.8	A	
$I_{T(AV)}$	Average on-state current (180° conduction angle)		0.5	A	
$I_{TSM}$	Non repetitive surge peak on-state current, $T_j$ initial = 25 °C	$T_j = 25\text{ °C}$	$t_p = 8.3\text{ ms}$	8	A
			$t_p = 10\text{ ms}$	7	
$I^2t$	$I^2t$ value for fusing	$t_p = 10\text{ ms}$	$T_j = 25\text{ °C}$	0.24	A <sup>2</sup> s
$di/dt$	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$ , $t_r \leq 100\text{ ns}$	$F = 60\text{ Hz}$	$T_j = 25\text{ °C}$	50	A/ $\mu$ s
$V_{DRM} / V_{RRM}$	Repetitive peak off-state voltage		$T_j = 125\text{ °C}$	400	V
$I_{GM}$	Peak gate current	$t_p = 20\text{ }\mu$ s	$T_j = 125\text{ °C}$	1	A
$P_{G(AV)}$	Average gate power dissipation		$T_j = 125\text{ °C}$	0.1	W
$T_{stg}$	Storage junction temperature range			-40 to +150	°C
$T_j$	Operating junction temperature range			-40 to +125	°C

**Table 2. Electrical characteristics ( $T_j = 25\text{ °C}$ , unless otherwise specified)**

Symbol	Parameters	Value	Unit	
$I_{GT}$	$V_D = 12\text{ V}$ , $R_L = 33\text{ }\Omega$	Max.	200	$\mu$ A
$V_{GT}$		Max.	0.8	V
$V_{GD}$	$V_D = V_{DRM}$ , $R_L = 3.3\text{ k}\Omega$ , $R_{GK} = 1\text{ k}\Omega$ , $T_j = 125\text{ °C}$	Min.	0.1	V
$V_{RG}$	$I_{RG} = 10\text{ }\mu$ A	Min.	8	
$I_H$	$I_T = 50\text{ mA}$ , $R_{GK} = 1\text{ k}\Omega$	Max.	5	mA
$I_L$	$I_G = 1.2 I_{GT}$ , $R_{GK} = 1\text{ k}\Omega$	Max.	6	mA
$dV/dt$	$V_D = 67\% V_{DRM}$ , $R_{GK} = 1\text{ k}\Omega$ , $T_j = 125\text{ °C}$	Min.	75	V/ $\mu$ s

**Table 3. Static electrical characteristics**

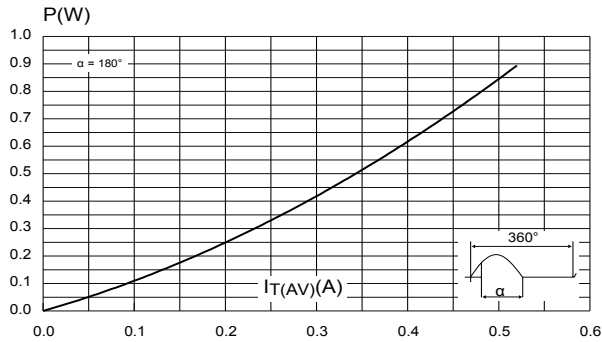
Symbol	Test conditions	$T_j$	Value	Unit
$V_T$	$I_{TM} = 1.6\text{ A}$ , $t_p = 380\text{ }\mu$ s	25 °C	Max. 1.95	V
$V_{TO}$	Threshold on-state voltage	125 °C	Max. 0.95	V
$R_d$	Dynamic resistance	125 °C	Max. 600	m $\Omega$
$I_{DRM}$	$V_D = V_{DRM}$	25 °C	Max. 1	$\mu$ A
$I_{RRM}$	$V_R = V_{RRM}$	125 °C		0.1

**Table 4. Thermal resistance**

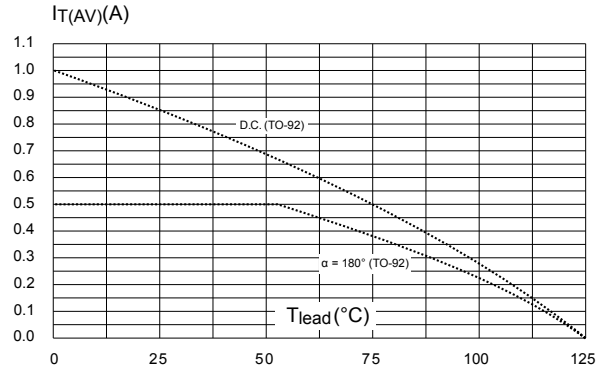
Symbol	Parameters	Max. value	Unit
$R_{th(j-l)}$	Junction to lead (DC)	80	°C/W
$R_{th(j-a)}$	Junction to ambient (DC)	150	

**1.1 Characteristics (curves)**

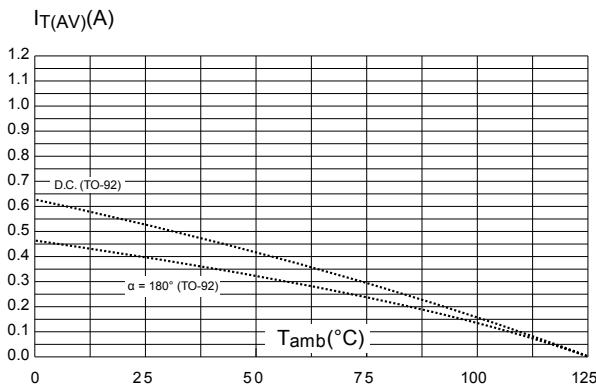
**Figure2. Maximum power dissipation versus on-state RMS current (full cycle)**



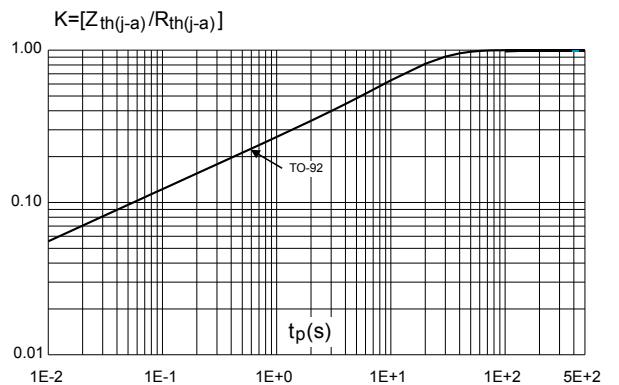
**Figure3. Average and DC on-state current versus lead temperature**



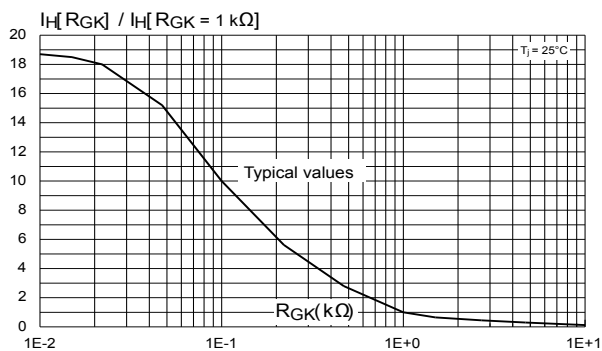
**Figure 4. Average and DC on-state current versus ambient temperature**



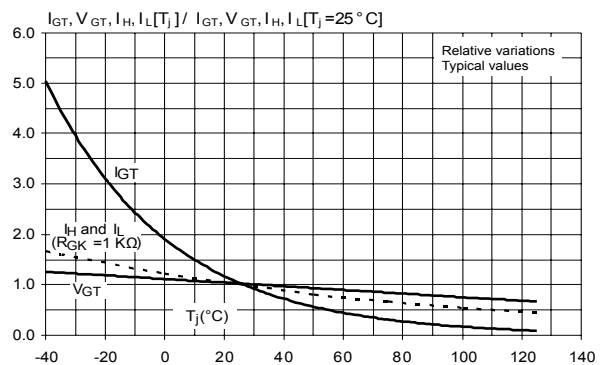
**Figure5. Relative variation of thermal impedance versus pulse duration**



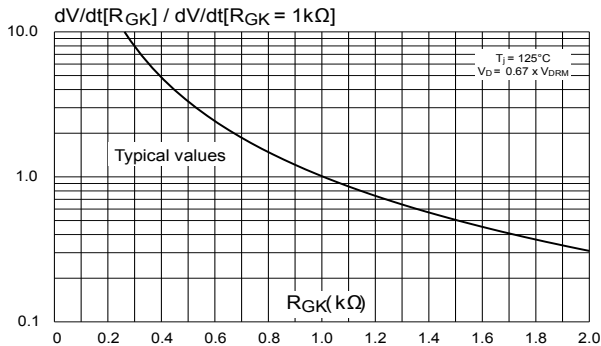
**Figure6. Relative variation of holding current versus gate-cathode resistance**



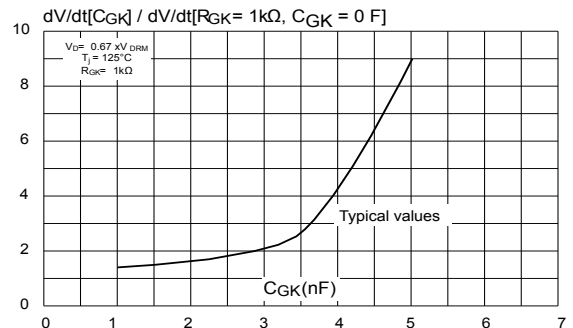
**Figure7. Relative variation of gate voltage and gate, holding and latching current versus junction temperature**



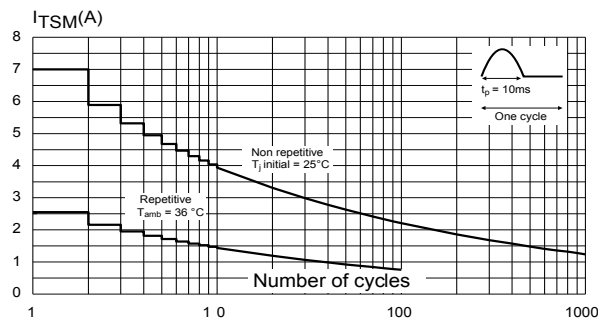
**Figure8. Relative variation of static dV/dt immunity versus gate-cathode resistance**



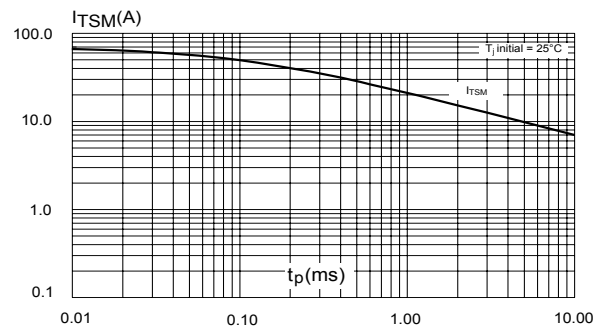
**Figure9. Relative variation of dV/dt immunity versus gate-cathode capacitance**



**Figure10. Surge peak on-state current versus number of cycles**



**Figure 11. Non-repetitive surge peak on-state current for sinusoidal pulse ( $t_p < 10\text{ ms}$ )**



**Figure12. On-state characteristics (maximum values)**

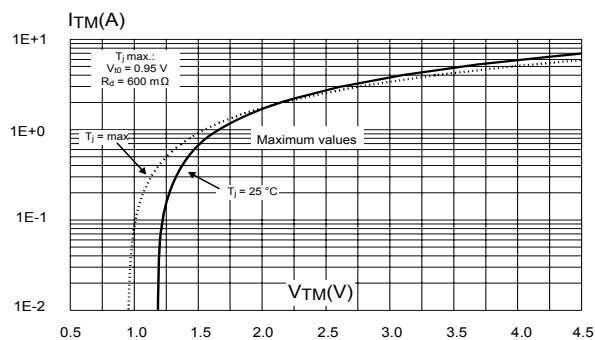


Figure 13. TO-92 package outline

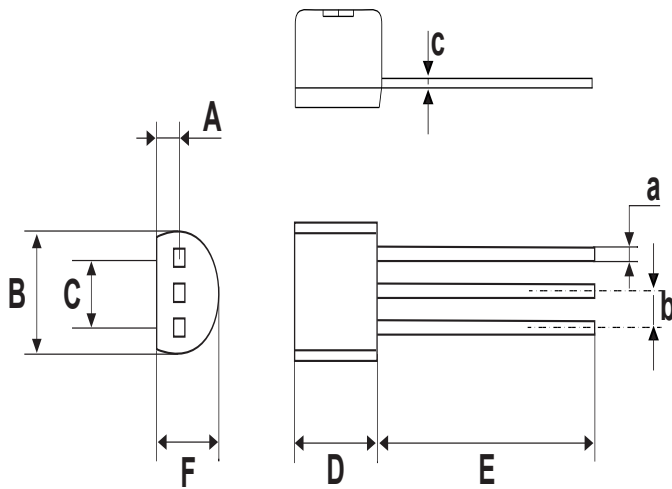


Table 5. TO-92 package mechanical data

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A		1.35			0.0531	
B			4.70			0.1850
C		2.54			0.1000	
D	4.40			0.1732		
E	12.70			0.5000		
F			3.70			0.1457
a			0.50			0.0197
b		1.27			0.0500	
c			0.48			0.0189

1. Inches dimensions given for information

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